Silicon N Channel Power MOS FET High Speed Power Switching

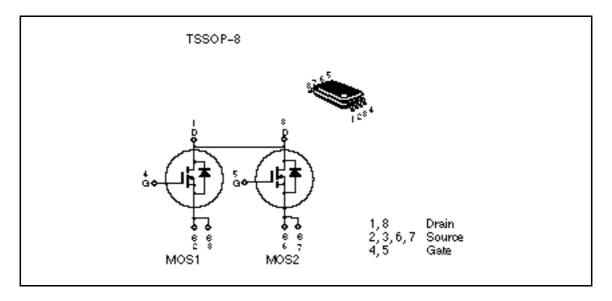


ADE-208-669F (Z) 7th. Edition February 1999

Features

- Low on-resistance
- Capable of 2.5 V gate drive
- Low drive current
- High density mounting

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	28	V
Gate to source voltage	V _{GSS}	±12	V
Drain current	I _D	5.0	А
Drain peak current	Note1 D(pulse)	40	А
Body-drain diode reverse drain current	I _{DR}	5.0	А
Channel dissipation	Pch Note2	1.0	W
Channel dissipation	Pch Note3	1.5	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

Note: 1. PW 10 μ s, duty cycle 1 %

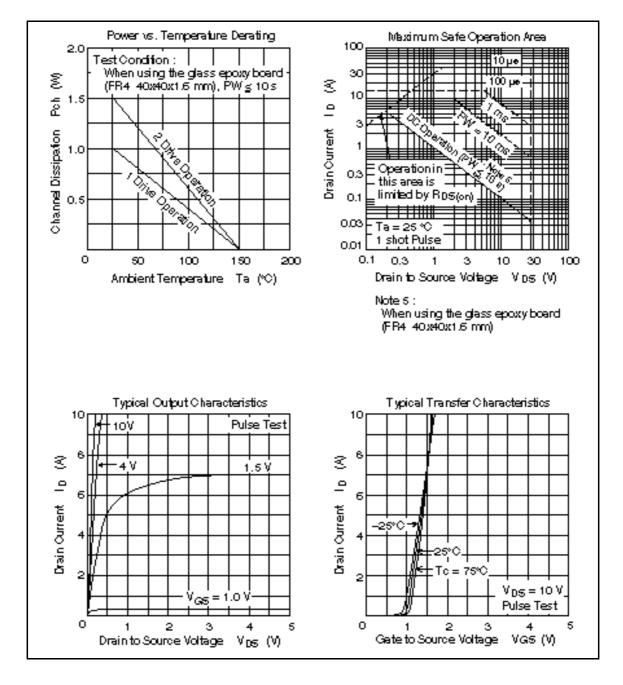
2. 1 Drive operation ; When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW 10s

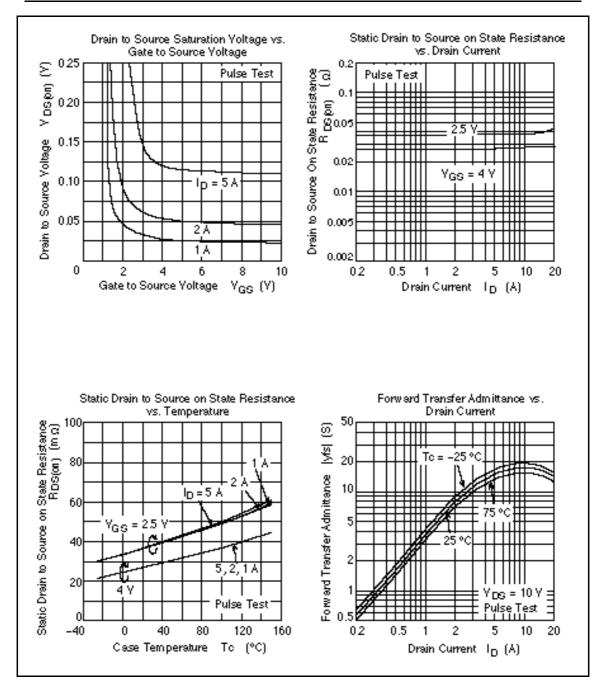
3. 2 Drive operation ; When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW 10s

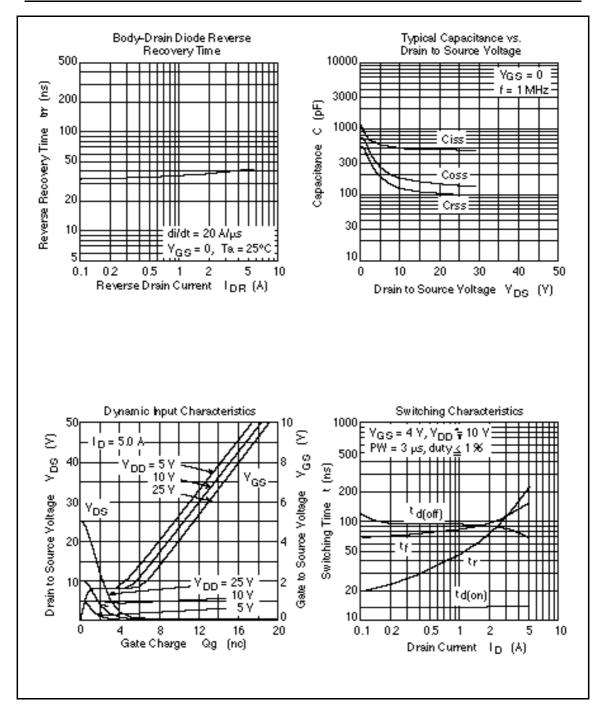
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{\rm (BR)DSS}$	28		_	V	$I_{\rm D} = 10 {\rm mA}, V_{\rm GS} = 0$
Gate to source leak current	I _{GSS}	—	—	±0.1	μA	$V_{GS} = \pm 12V$, $V_{DS} = 0$
Zero gate voltege drain current	I _{DSS}	—	—	1	μA	$V_{\rm DS} = 28 \ V, \ V_{\rm GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	0.4		1.4	V	$V_{DS} = 10V, I_{D} = 1mA$
Static drain to source on state	$R_{\text{DS(on)}}$	—	0.027	0.034		$I_D = 3A$, $V_{GS} = 4V^{Note4}$
resistance	$R_{\text{DS(on)}}$	_	0.037	0.044		$I_{\rm D} = 3A, V_{\rm GS} = 2.5V^{\rm Note4}$
Forward transfer admittance	y _{fs}	7	11	_	S	$I_D = 3A$, $V_{DS} = 10V^{Note4}$
Input capacitance	Ciss	—	510	_	pF	V _{DS} = 10V
Output capacitance	Coss	_	190	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	—	140	—	pF	f = 1MHz
Total gate charge	Qg	—	8.5	_	nc	$V_{DD} = 10V$
Gate to source charge	Qgs	_	4.5	_	nc	$V_{GS} = 4V$
Gate to drain charge	Qgd	—	4	_	nc	$I_{\rm D} = 5A$
Turn-on delay time	t _{d(on)}	_	14	_	ns	$V_{GS} = 4V, I_{D} = 3A$
Rise time	t,	—	120	_	ns	V _{DD} 10V
Turn-off delay time	$t_{d(off)}$	_	85	_	ns	_
Fall time	t _f	_	120	_	ns	-
Body–drain diode forward voltage	V_{DF}	—	0.85	1.1	V	IF =5.0A, $V_{GS} = 0^{Note4}$
Body–drain diode reverse recovery time	t _{rr}		40	_	ns	$IF = 5.0A, V_{GS} = 0$ diF/ dt =20A/µs

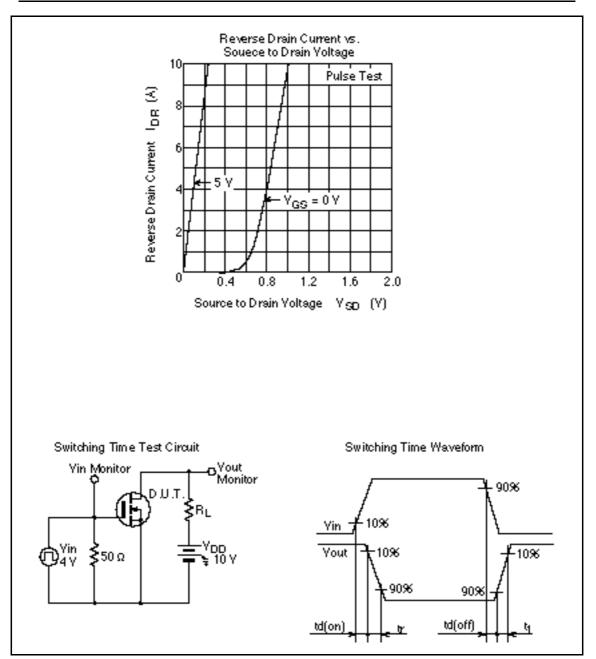
Note: 4. Pulse test

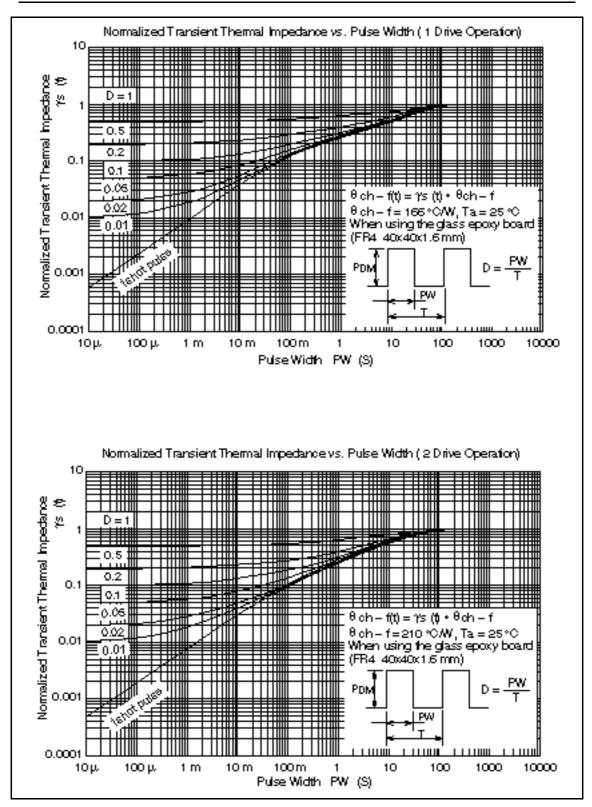
Main Characteristics





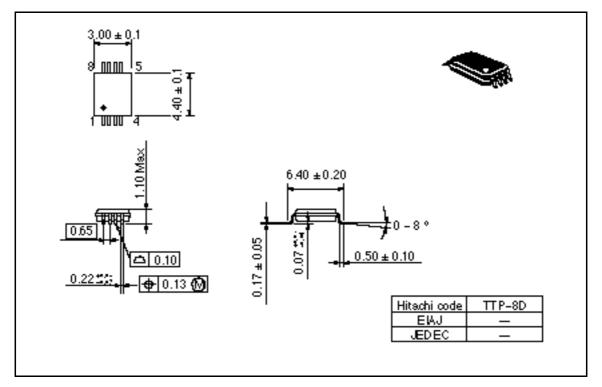






Package Dimensions

Unit: mm



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